

AMENDMENTS TO THE CLAIMS

1. (Original) A silicon electrode plate for plasma etching with superior durability, the silicon electrode plate comprising silicon single crystal which, in terms of atomic ratio, contains 3 to 11 ppba of boron, and further contains a total of 0.5 to 6 ppba of either or both of phosphorus and arsenic.

2. (New) A silicon electrode plate according to claim1, wherein said silicon single crystal comprises Si raw material with a purity of 11N, and boron, and either or both of phosphorus and arsenic.